Electronic Supplementary Material (ESI) for Physical Chemistry Chemical Physics.

Supplementary Information

Enhanced photoresponse of epitaxially grown ZnO by MoO_3 surface functionalization

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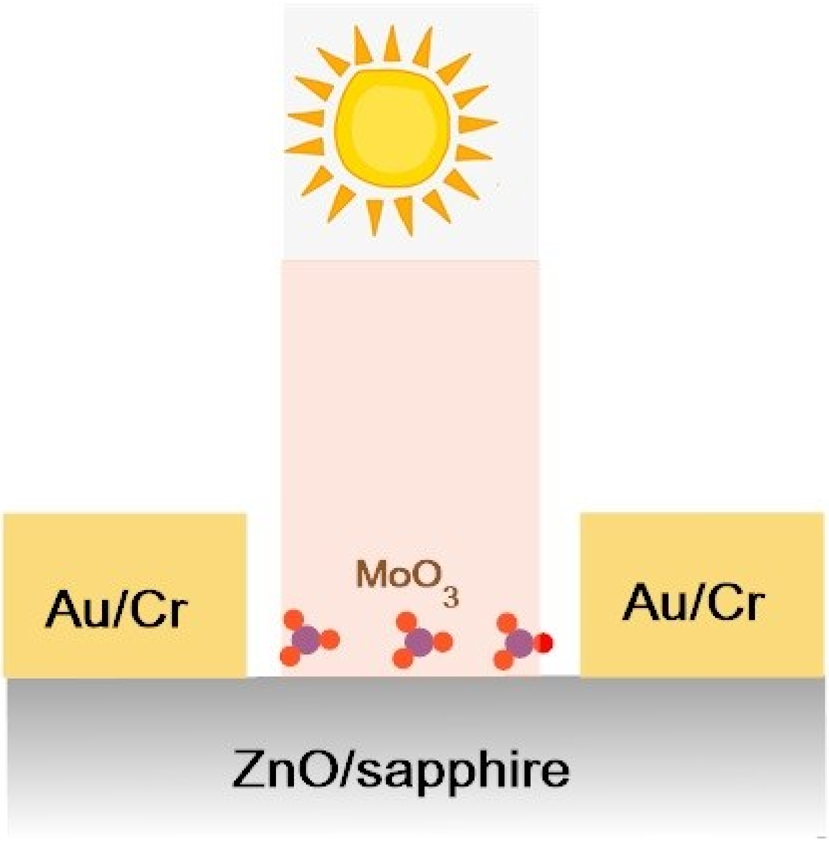

Figure S1 Schematic device structure of MoO_3 modified ZnO

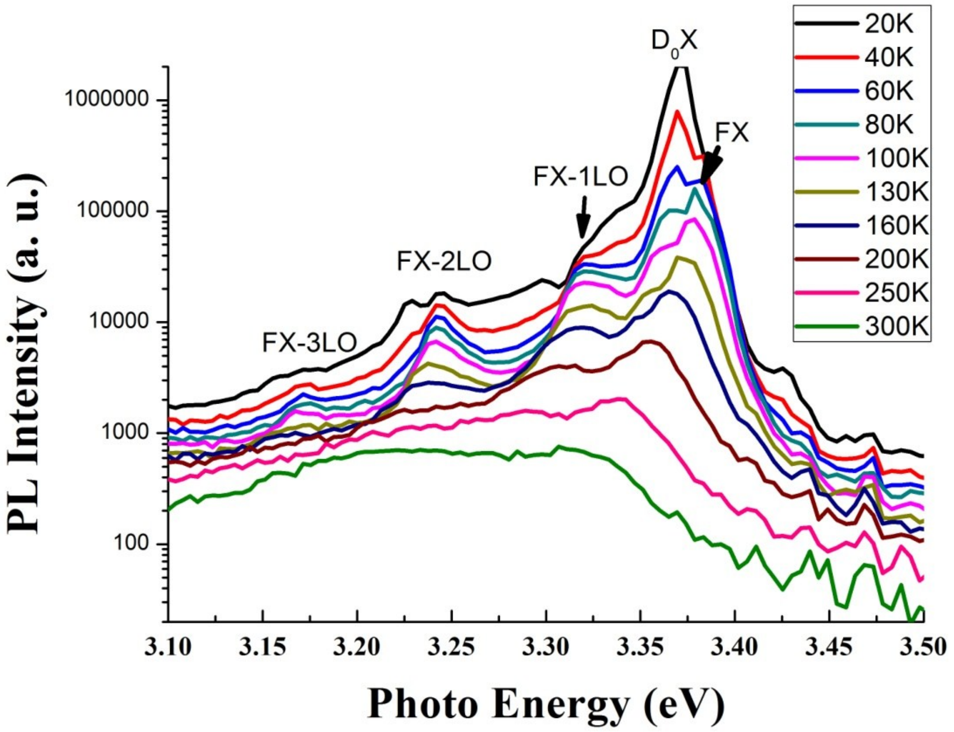

Figure S2 Temperature dependent PL spectra of 0.5 nm modified ZnO

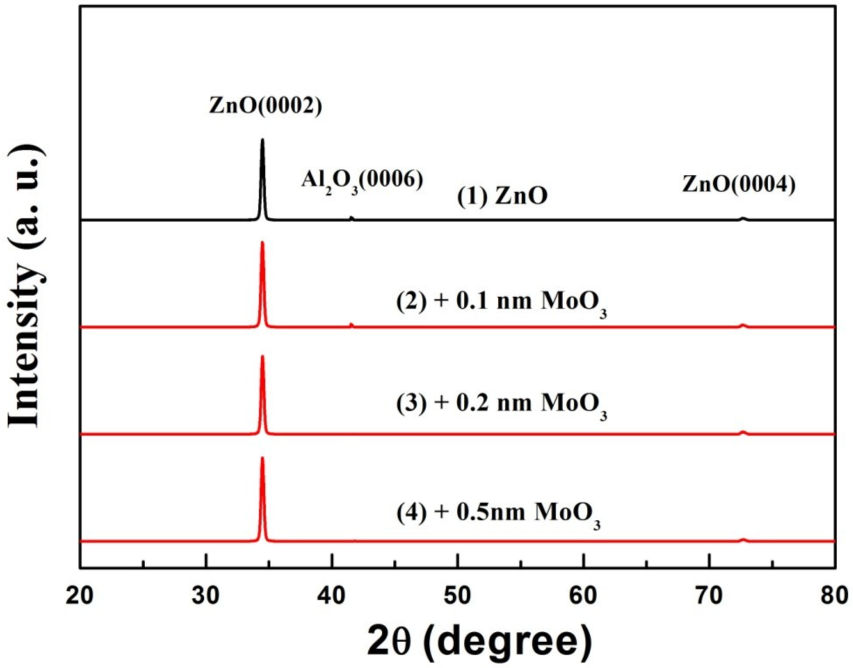

Figure S3 XRD spectra of ZnO thin film before and after the subsequential deposition of 0.5 nm MoO_3.

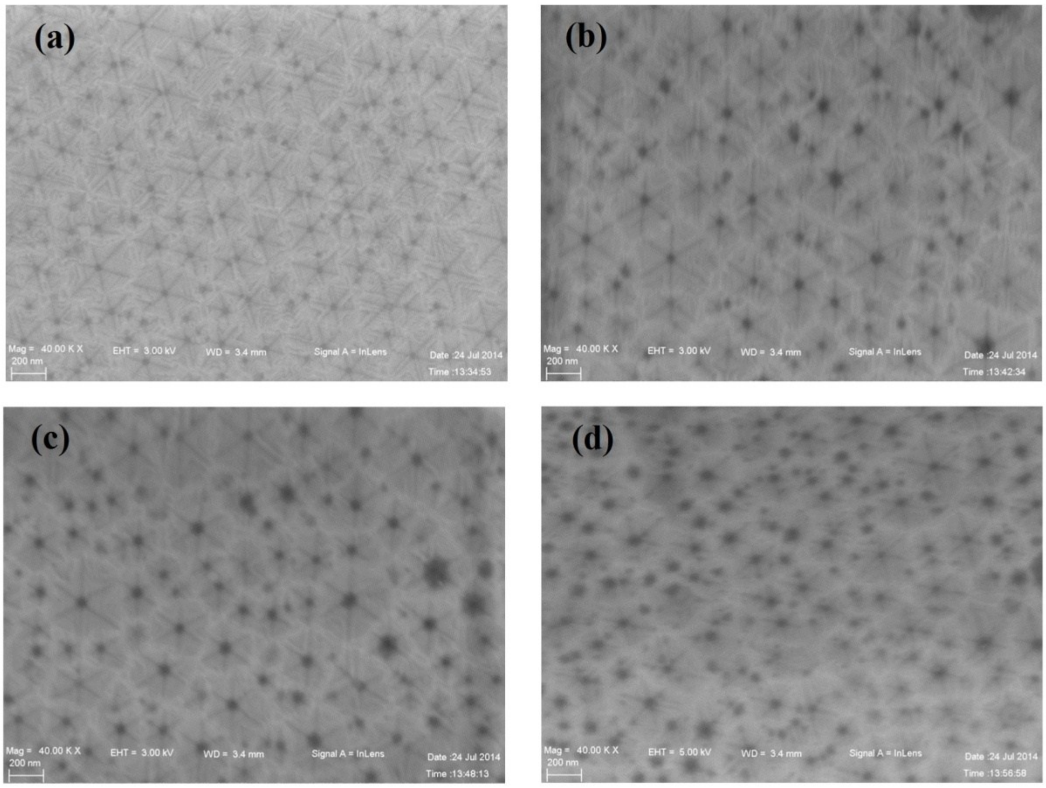

Figure S4 SEM images of (a) pristine ZnO and after (b) 0.1, (c) 0.2, and (d) 0.5 nm MoO_3 modification.